Predoctoral Position (MBE of GaSb integrated on Si PICs)

We are looking for a predoctoral researcher on the molecular beam epitaxy (MBE) **growth, design, and characterization** of **novel GaSb-based structures integrated** on **Silicon PICs** with emission in the Mid-Infrared region for applications such as **health care, biosensing and environmental monitoring**.

We offer a predoctoral position for a highly motivated researcher with strong track-record, strongly committed to contribute to a breakthrough project in **photonics** and **material science**.

The research will be carried out at the **Nanophotonics Technology Center** (https://ntc.webs.upv.es/) of the **Universitat Politècnica de València**, in collaboration with renowned partners. Research group (https://ntc.webs.upv.es/iii-v-semiconductors-and-graphene/)

REQUIREMENTS:

- Full professional competence in English.
- Ability to work both independently and collaboratively.
- Master degree in physics, materials/telecommunication engineering, chemistry or similar.

JOB CONDITIONS:

- Three-year contract; possibility of extension.
- Annual Gross Salary: 18,000 € - 22,000 €; commensurate with experience.
- Health and Social benefits included according to Spanish law.
- Work in a highly competitive international environment.
- Full access to a Unique Scientific and Technical Facility of the Spanish Government: ICTS MICRONANOFABS, NTC-UPV node (https://micronanofabs.org/en/home-2/)

Should you are interested, please **send us your CV and motivation letter:**

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